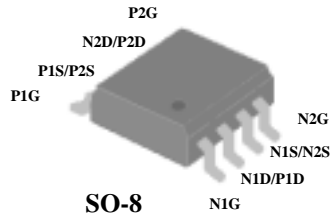


## 2N AND 2P-CHANNEL ENHANCEMENT MODE POWER MOSFET

### PRODUCT SUMMARY

Simple Drive Requirement  
Low On-resistance  
Full Bridge Application on  
LCD Monitor Inverter

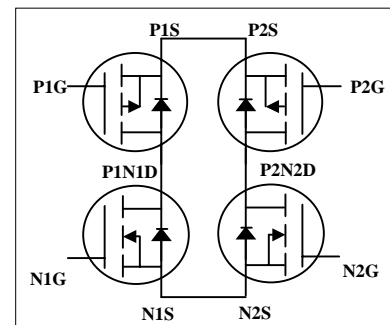


N-CH	$BV_{DSS}$	35V
	$R_{DS(ON)}$	48m $\Omega$
	$I_D$	4.3A
P-CH	$BV_{DSS}$	-35V
	$R_{DS(ON)}$	72m $\Omega$
	$I_D$	-3.6A

### DESCRIPTION

The advanced power MOSFETs from Silicon Standard Corp. provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



 **Pb-free; RoHS-compliant**

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
$V_{DS}$	Drain-Source Voltage	35	-35	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current <sup>3</sup>	4.3	-3.6	A
$I_D@T_A=70^\circ C$	Continuous Drain Current <sup>3</sup>	3.4	-2.8	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	20	-20	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	1.38		W
	Linear Derating Factor	0.01		W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ C$

### THERMAL DATA

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 90	$^\circ C/W$

## N-CH ELECTRICAL CHARACTERISTICS

@T<sub>j</sub>=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	35	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.03	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =4A	-	-	48	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	-	70	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =4A	-	8	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
	Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =4A	-	6	10	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =28V	-	2	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	3	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =15V	-	6	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	5	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	14	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	4	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	490	780	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	130	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	55	-	pF

## SOURCE-DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.2A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =4A, V <sub>GS</sub> =0V	-	18	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	11	-	nC

## P-CH ELECTRICAL CHARACTERISTICS

@T<sub>j</sub>=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-35	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	-	-0.02	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	-	-	72	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	-	-	100	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-	-3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A	-	6	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T=25°C)	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	uA
	Drain-Source Leakage Current (T=70°C)	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =-3A	-	6	10	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-28V	-	1	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	3	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =-15V	-	7	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =-1A	-	5	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =-10V	-	19	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	4	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	420	1100	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-25V	-	140	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	65	-	pF

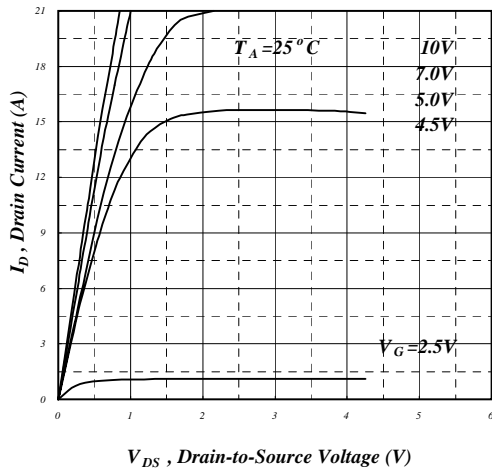
## SOURCE-DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =-1.2A, V <sub>GS</sub> =0V	-	-	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =-3A, V <sub>GS</sub> =0V	-	20	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=-100A/μs	-	16	-	nC

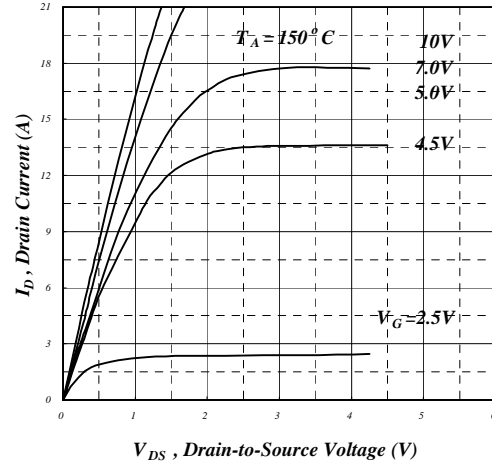
### Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse width ≤300us, duty cycle ≤2%.
3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t ≤10sec; 186 °C/W when mounted on Min. copper pad.

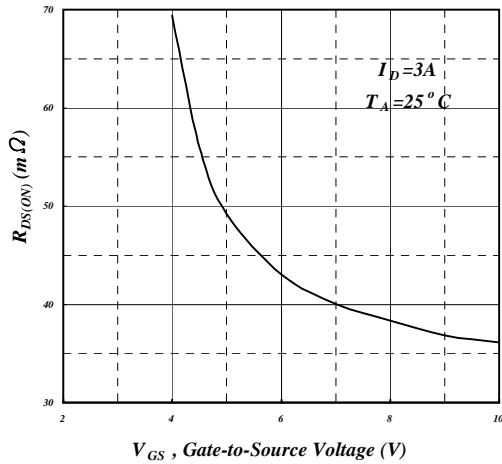
**N-Channel**



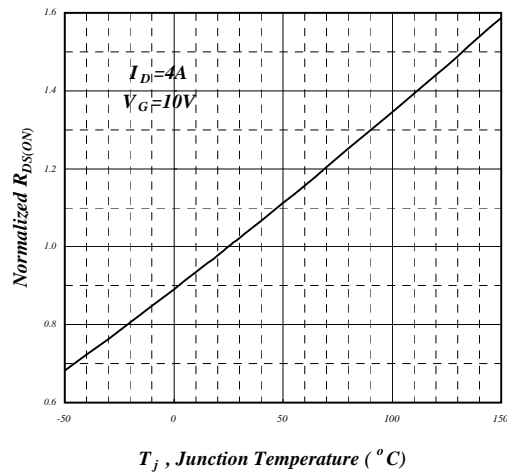
**Fig 1. Typical Output Characteristics**



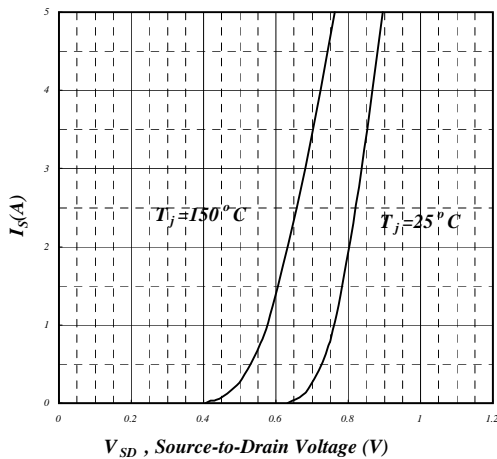
**Fig 2. Typical Output Characteristics**



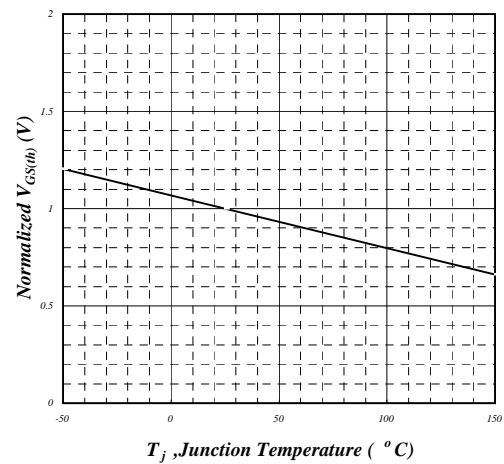
**Fig 3. On-Resistance v.s. Gate Voltage**



**Fig 4. Normalized On-Resistance v.s. Junction Temperature**

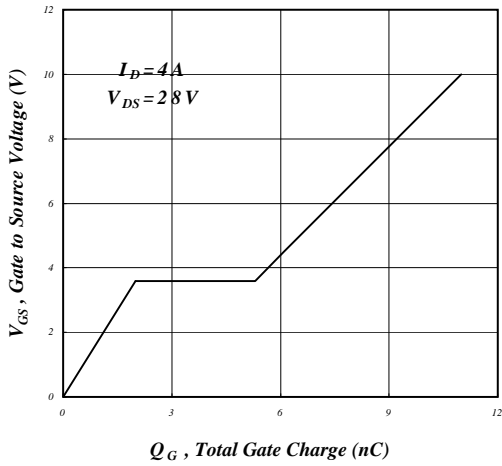


**Fig 5. Forward Characteristic of Reverse Diode**

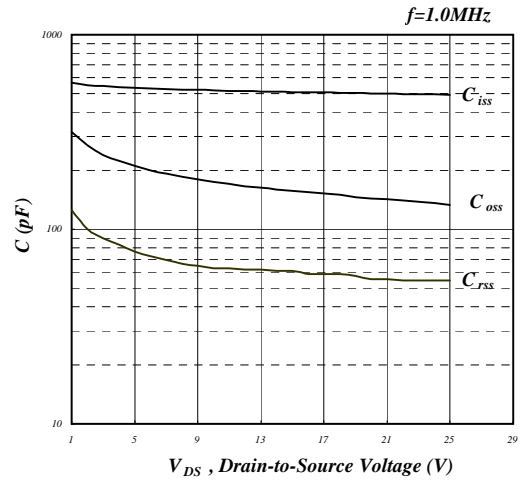


**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**

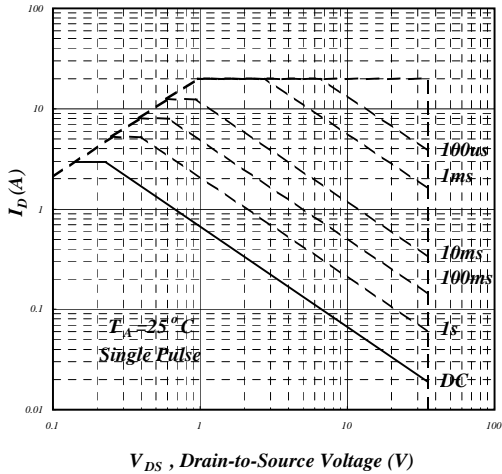
**N-Channel**



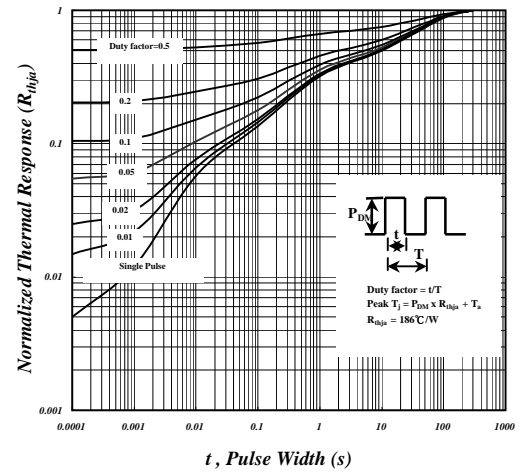
**Fig 7. Gate Charge Characteristics**



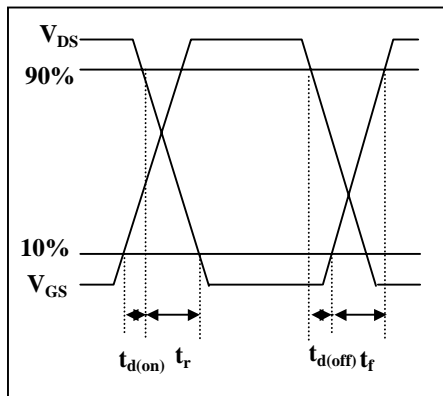
**Fig 8. Typical Capacitance Characteristics**



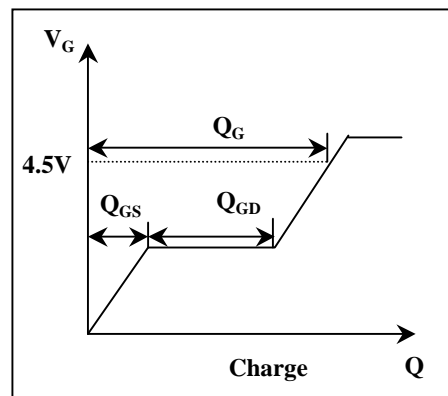
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**

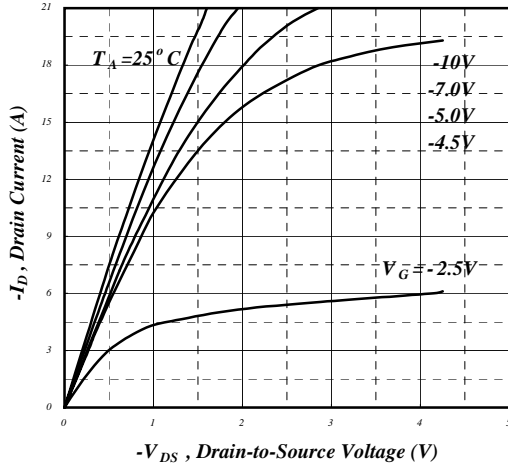


**Fig 11. Switching Time Waveform**

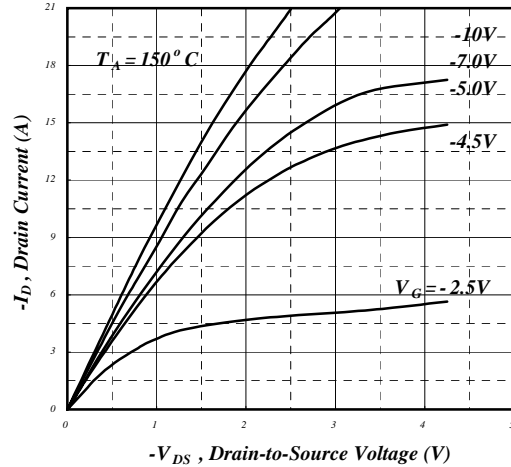


**Fig 12. Gate Charge Waveform**

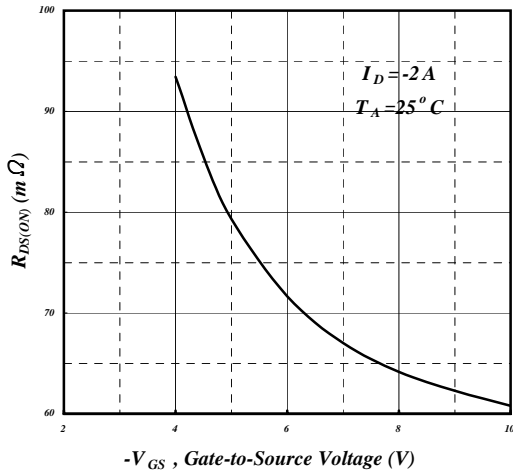
**P-Channel**



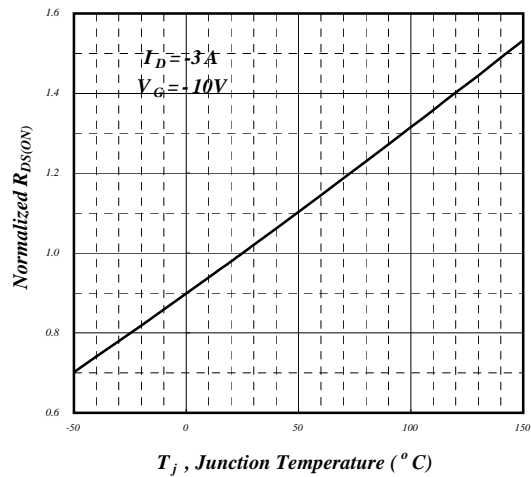
**Fig 1. Typical Output Characteristics**



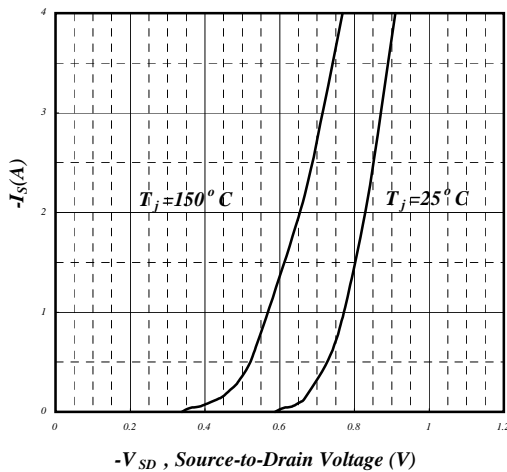
**Fig 2. Typical Output Characteristics**



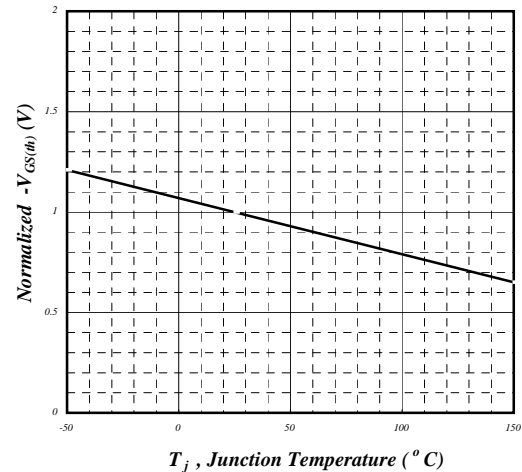
**Fig 3. On-Resistance v.s. Gate Voltage**



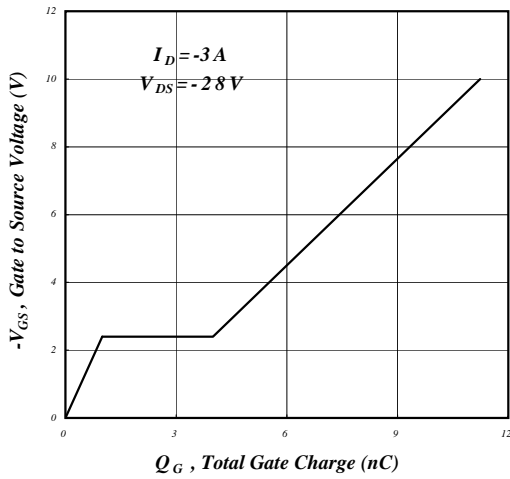
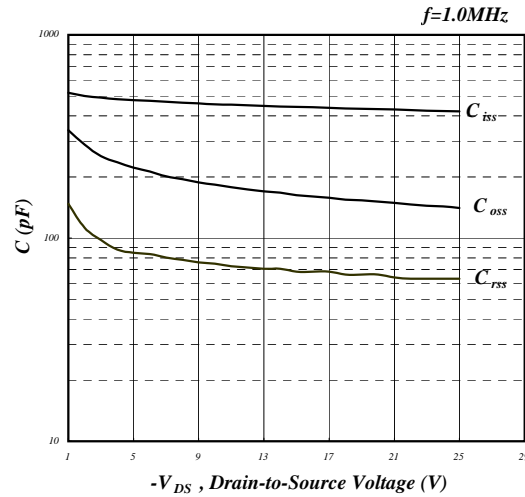
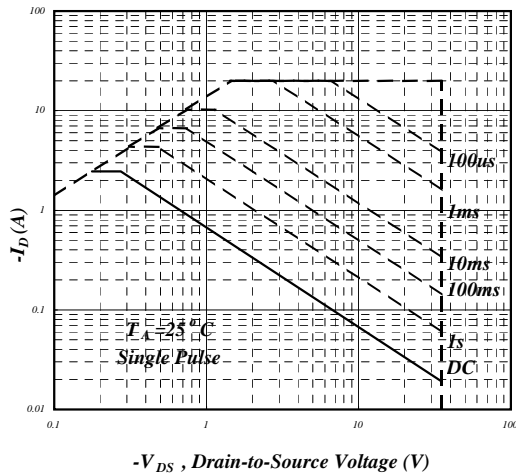
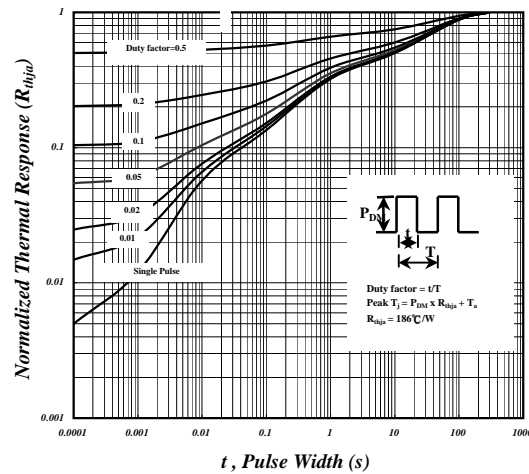
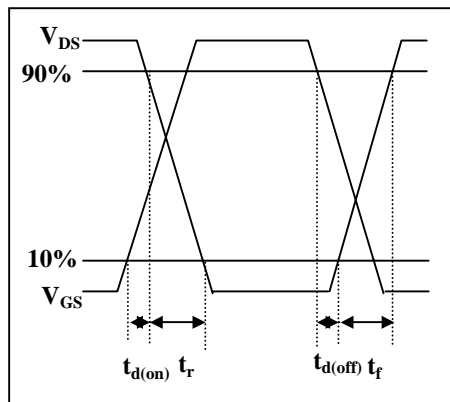
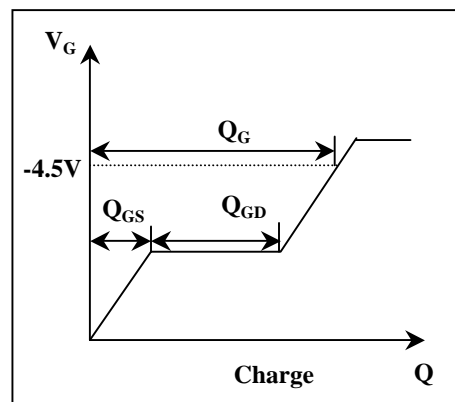
**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



**Fig 5. Forward Characteristic of Reverse Diode**



**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**

**P-Channel**

**Fig 7. Gate Charge Characteristics**

**Fig 8. Typical Capacitance Characteristics**

**Fig 9. Maximum Safe Operating Area**

**Fig 10. Effective Transient Thermal Impedance**

**Fig 11. Switching Time Waveform**

**Fig 12. Gate Charge Waveform**

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